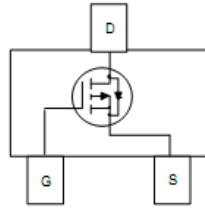
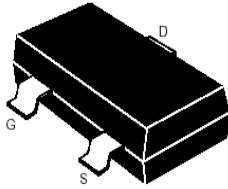


SOT-23

Features

- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance

MAXIMUM RANTINGS

Characteristic	Symbol	Max	Unit
Drain-Source Voltage	BV_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 20	V
Drain Current (continuous)	I_D	-4.1	A
Drain Current (pulsed)	I_{DM}	-16	A
Total Device Dissipation $T_A=25^\circ C$	P_D	1400	mW
Junction	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55to+150	$^\circ C$

Electrical Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage ($I_D = -250\mu A, V_{GS}=0V$)	BV_{DSS}	-30	—	—	V
Gate Threshold Voltage ($I_D = -250\mu A, V_{GS}=V_{DS}$)	$V_{GS(th)}$	-1	—	-2.5	V
Diode Forward Voltage Drop ($I_S = -1 A, V_{GS}=0V$)	V_{SD}	—	—	-1	V
Zero Gate Voltage Drain Current ($V_{GS}=0V, V_{DS} = -24V$) ($V_{GS}=0V, V_{DS} = -24V, T_A=25^\circ C$)	I_{DSS}	—	—	-1 -5	μA
Gate Body Leakage ($V_{GS}=\pm 20V, V_{DS}=0V$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance ($I_D = -4.1A, V_{GS} = -10V$)	$R_{DS(ON)}$	—	55	65	$m\Omega$
Static Drain-Source On-State Resistance ($I_D = -2A, V_{GS} = -4.5V$)	$R_{DS(ON)}$	—	75	95	$m\Omega$
Input Capacitance ($V_{GS}=0V, V_{DS} = -15V, f=1MHz$)	C_{ISS}	—	260	—	pF
Output Capacitance ($V_{GS}=0V, V_{DS} = -15V, f=1MHz$)	C_{OSS}	—	37	—	pF
Turn-ON Time ($V_{DS} = -15V, I_D = -10 A, R_{GEN}=6\Omega$)	$t_{(on)}$	—	6	—	ns
Turn-OFF Time ($V_{DS} = -15V, I_D = -10 A, R_{GEN}=6\Omega$)	$t_{(off)}$	—	20	—	ns

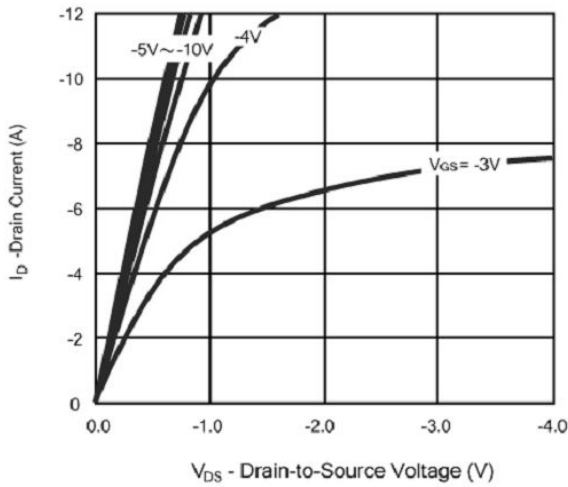


Figure 1: Output Characteristics

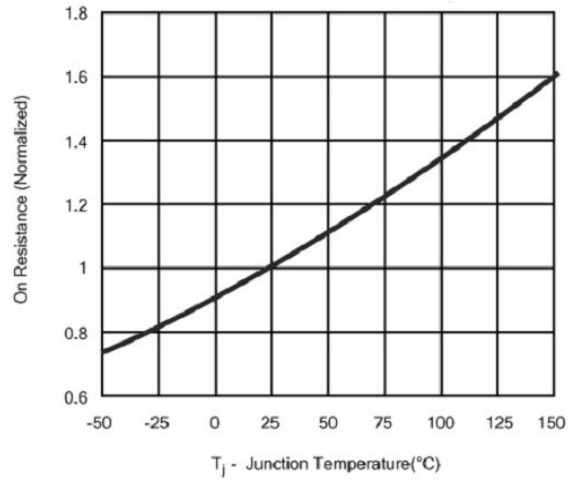


Figure 2: On-Resistance vs. Junction Temperature

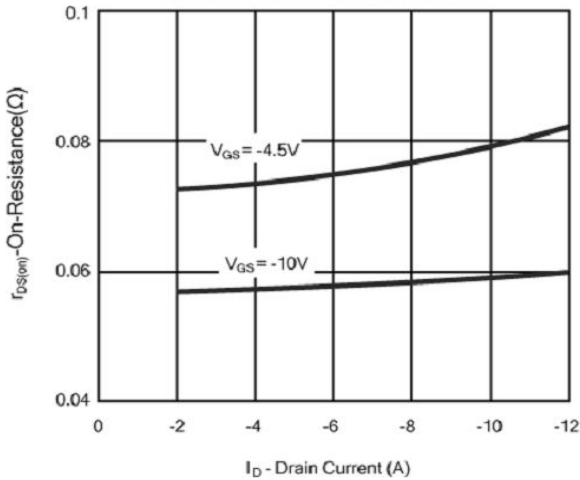


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

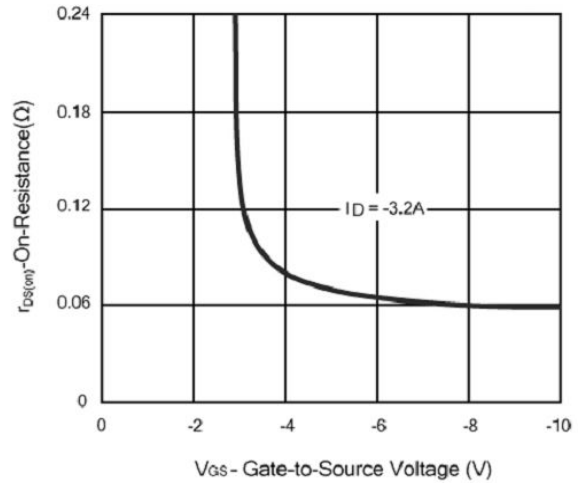


Figure 4: On-Resistance vs. Gate-Source Voltage

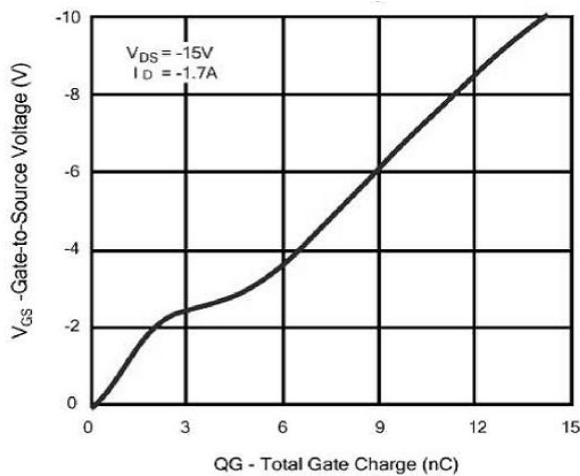


Figure 5: Gate-Charge Characteristics

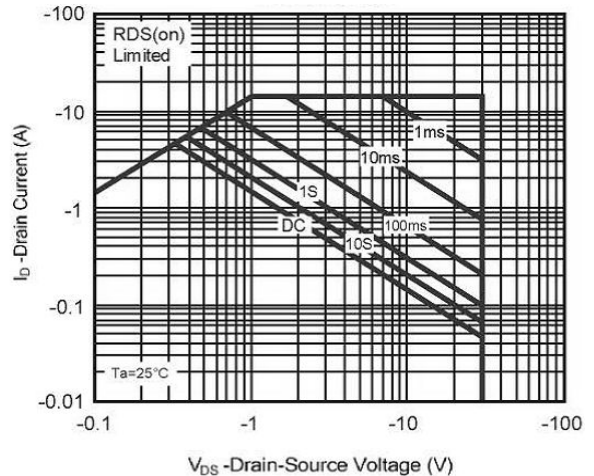
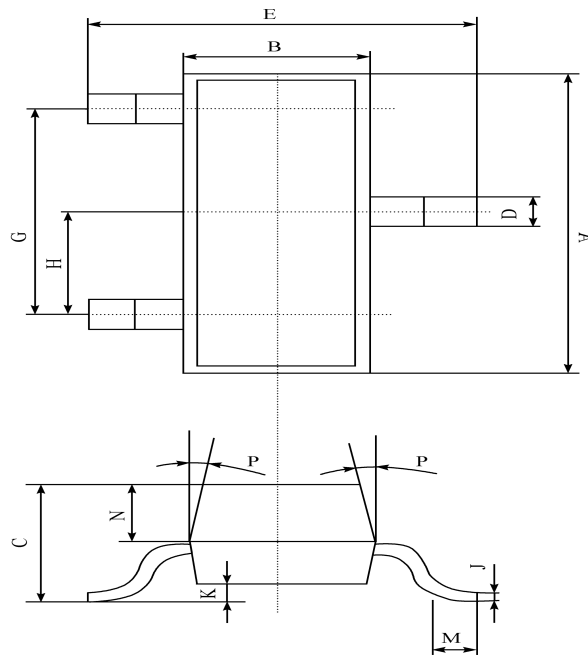


Figure 6: Safe Operating Area

SOT-23 PACKAGE OUTLINE Plastic surface mounted package



SOT-23	
A	2.90 ± 0.10
B	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
E	2.40 ± 0.20
G	1.90 ± 0.10
H	0.95 ± 0.05
J	0.13 ± 0.05
K	0.00-0.10
M	≥ 0.2
N	0.60 ± 0.10
P	7 ± 2°

(UNIT): mm

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Bourne](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#)
[424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#)
[IPS70R2K0CEAKMA1](#) [RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#)
[NTE6400](#) [JANTX2N6796U](#) [JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#)